CTE mismatch

between chip and substrate is the root cause for reliability issues in flip chip packages, such as excessive warpage, low dielectric layer cracksolder mask cracking, and bump cracking. The first and foremost thing in designing a flip chip package is to control excessive warpagevarpaget the specification this paper, a capipedup chip package is proposed to control the warpage deals to reduce the stress. In the pedie flip chip package tal cap tightly covers and bonds with the die through an adhesive material. As a result, the cadiped das a higher effective ByCTE. adjusting the thicknesset of cap, the effective of the cappedie can matchwith the TCE of substrate, theoretically achievingwaepage or warfrageTo verify the appedie concept for envarpage control, 45mmx45mm sizeappedieflip chip packasgelesigned and manufactubesed on the guidance infitementer modeling, where a coppeap divith 0.4mm thickness is selected. This hado Moiré test is performed to measure the warpaas function of temperatures from 260 c. Experimental data show that in them the ature range the warpage curve of the cappedie package is almost flatJ ET BT 1 0 0 1 259.61636(ce)-3(p)-5(t)-302(f)45.7



warpageIn Figure 2, (a), (b) and (c) show the basic assembly ethod, which will introduce an additional stress into the steps of a flip chip package, when the tstep (a) is for die attach package.

process, the step (b)is for underfill dispensing and curing process, and the step (or) (d) is for stiffener/lid attachment process. After the die attastep (a), the electrical connection between the die and substrate homesen completed and the warpage at this point is small due to the quick relaxation of the solder bump stress that is caused by the visitian property of the solder material n other words the die attachstep (a) completes the electrical connection between the die an substrate, but the mechanical connection is werakerder to enhance the valk mechanical connectido protect the solder bumps, the underfill is filled into the gap between the die and substrate. Solte application of underfill in the step (b) is only for the reliability of the electrical connection from the mechanical viewpointThe underfill is usually wred at a high temperature, such as 5 C. The flip chip package during the underfill curing process is very flat, i.ethe warpage at the point is very small due to the same reason as the voisastic property of the solder material. However, after the underfill is

cured, the die and substrate are strongly connected mechanical viewpointThen, when cooling down to the room temp or rising up to the reflow temperature, the warpage will be developed due to the big CTE differenecbetween the die and substrate of example the downwards warpage at room Capped Die Flip chip Package Design temperature (also called coplanaiissue) is shown in Figure 2 (b). JEDEC specification has definesmil or 200um for large flip chip packageas the tolerance limit. However, far 45mmx45mm size of flip chip package bare die FCBGA can have a warpagever 12mil or 300um. The excessive shownin Figure 3, and an assembly process appeedie flip warpage may cause a lot of issues in board level of operations, package as shown in Figure 4. The assembly process of such as solder ball bridging or opening during surface mourappeddie flip chip packages includes these steps) (a process, failures during package functional testreduce the warpage, a stiffener ring or a lid is conventionally applied is ubstrate, (b dispensing adhesive material on the top of the the next processing step after underfill curing process, die, (d) covering the die cap onto the die, and (add not underfill) showed in Figure 1 (b) or (c). The mechanism of using a curing theunderfill and adhesive materials. stiffener or lid to reduce the warpage is illustrated in Figure 2 (c) and (d) where the stiffener or lid applies a force torque it is seenthat theconventionalways using a stiffener or lid to mainly constrain the die, forming cappeddie, or says it is a reduce the warpage is a way tedreform the substrate, or saysdie control method, and the second is thathe underfill the flip chip package rises when the substrate-istefermed by the siffener or lid. For example, ofr the FCBGA with 45mmx45mm substrate size and 23mmx23mm die size, they get matched, and he warpage after the underfill for the package types of bare dietiffener and lid, respectively. Though the Lidded FCBGAgives the lowest warpage, it causes highest stress in package, as compared give a good joint of both underfill and adhesivenaterials at the bare die and stiffener packages.

In summary there are three point about the warpage control by using stiffener or lithat need to be keptin mind: (1) warpage habeendeveloped after underfill dispering and curing process. This means the arpage has been frozen in the package(2) stiffener or lid attachprocess is done after underfill curing process and β) the conventional ways using stiffener or lid to control warpage is only to redeform the substrate Therefore, the above methods are substraterol



Figure 2. Assembly processes blip chip package and mechanism of conventionalways for wapage control: (a) die attactb) undefill dispensingand curing, and (c) Stiffener or ladtach

A cappeddie flip chip package is designed based on the preceding analysis for the mechanism of warpageecially the three points of conventional warpage control mechanism, which includes a structure of cambdie flip chip packageas dispensing underfill material into the gaptween the die and

It is seen that there are two key differencethefcapped die flip chip package designment the conventional flip chip at the edge of the substrate, forcing it to deform upwards. Stackages using stiffener or little first one is that the die cap it is a substrate control method. As a result, the stress level material between the die and the substrate and the adhesive material between the die cap and die are concurrently cured. As a result the CTE between the apped die anthe substrate warpage at room temperature are about 12mil, 8mil and 5rdispensing and curing press as showed in Figure 2(b) may been avoidedbefore it is frozen in the package if a die cap with a proper thikeness is selected. he same base resin can the die edge region.



Figure 3.A cappeddie flip chip package



Figure 4.Assemblyprocess for cappedie flip chip package.

Some potentialfailure modes of appeddie flip chip packages are illutrated in Figure 5. The reason for the possible failure modes is that a high stress may take place around the die edge regiowhen the die caponstrains the deformation of the die during temperature change. Based on this consideration, an improved diepcies designed to lessen the risk of the failure modes. The cappedied flip chip packages usig an improved die cap is shown in Figure 6



Figure 5 Potentialfailure modes for cappedie flip chip package



Figure 6 A cappeddie flip chip packagesing an improvedie cap design.

It is suggested that adhesive material should have the same Tg as that of the underfill material so that both materials consistentlybecome softer or harder when tematere passes Tg. It is preferred thaboth materials use the same resin as their base materials and their fillers may be different. For





under application or test loading conditions, improving the reliability of bumps and lowk layers of the package.

Finally, it is explained why the cappetite package ests stable at the small warpage value 65 lum fact, the warpage value is the warpage of the flip chip package at curing temperature 165 C. It is seen from Figure 8 that the bare die package is just having the warpage value around the temperature. The wange value of the capped die package no

Figure 10A.Contour plot of the deformation of the big size of package at room and high temperatures.

Figure 10B.Contour plotof the deformation of the medium size of package at room and high temperatures.

Figure 10C.Contour plot of the deformation of the small size of package at room and high temperatures.

(3) Effect of the thickness of die cap

In the preceding sectin for achieving warpaginee packaging the die cap tickness is selected by trial and error method through multiplerounds of simulations. Here, an interesting phenomenon, called/ex-controlled warpage is shown about warpage ontrol by capped lie when athicker die cap is selected the simulation example, the same big package is used, but a thinner substrate core, 0.4mm thickness of core is considered. It has been seen that for 0.8mm thickness of core, 0.4mm thickness of die cap gives an ideal warpage control. The simulation shows a phenomenon of over-controlled warpage by the same 0.4mm thickness of die cap for the package with the thinner core, as showing Figure 11(b). For the thin core, a thinner die cap, i.e., a 0.3mm thickness of die cap is propter an ideal warpage control, as shown in Figure 11(). Note that the conventional stiffener and lid 0 0-5(w)23(1071a)-269(0)-5(.)-2(3)-4()-26(BT 1 0 0 1 48-4()-26(BT 1 0 0 1 48-4(p//P << /MCa)-269(0(iv)7(es)T 1 0 07)



Figure 12. Contour plot of the deformation of big package using 8 layers of coreless substrate atmotemperatures.



Figure 13. Contour plot of the deformation of small package using 6 layers of coreless substrate at room temperatures.

Conclusions

The experimental and simulation results show that warpagefree packaging in the full range of the perture variation can be achieved by using capplied flip chip package design More experimental studies about the capped die flip chip package design are needed, especially for its possible failure modesSome major design considerations include the election of adhesive material for bonding the die cap with the diea proper thickness of die cap, and a proper gap between the die cap side and the die edge. The assembly process needs to be carefully performed to avoid the voids between the die cap and the die because both adhesive and in